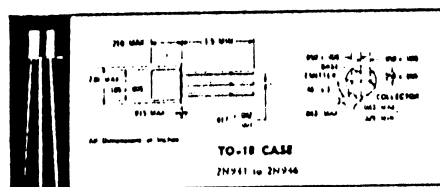
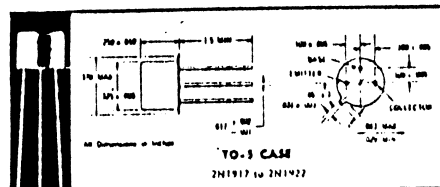


<h2 style="margin: 0;">SWITCHING</h2> <h3 style="margin: 0;">SILICON EPITAXIAL JUNCTION</h3> <h3 style="margin: 0;">PNP TRANSISTORS</h3>	2N941 — 2N1917 2N942 — 2N1918 2N943 — 2N1919 2N944 — 2N1920 2N945 — 2N1921 2N946 — 2N1922
--	--

- LOW AND HIGH LEVEL CHOPPING
- LOW JUNCTION CAPACITANCE



**ELECTRICAL DATA ABSOLUTE MAXIMUM RATING**

PARAMETER	SYMBOL	2N941/942 2N1917/1918	2N943/944 2N1919/1920	2N945 2N1921	2N946 2N1922	UNITS
Collector to Emitter Voltage	$BV_{CEO}$	-8	-18	-50	-80	V
Collector to Base Voltage	$BV_{CBO}$	-25	-40	-50	-80	V
Emitter to Base Voltage	$BV_{EBO}$	-25	-40	-50	-80	V
Collector Current	$I_C$	50mA				
Power Dissipation (free air)	$P_D$	250mW				
Junction Temp. (Oper. & Store)	$T_J$	-65°C to +175°C				
Lead Temp. (1/16" x 1/32" From Case)	$T_L$	240°C for 10 sec.				
Derating Factor (free air)	$D_r$	1.6mW/°C				

**ELECTRICAL CHARACTERISTICS:  $T_A = 25^\circ\text{C}$  (UNLESS OTHERWISE STATED)**

PARAMETER	SYMBOL	Case: TO-18 Case: TO-5	2N941 2N1917		2N942 2N1918		2N943 2N1919		2N944 2N1920		2N945 2N1921		2N946 2N1922		UNITS
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Collector-Base Leakage Current	$I_{CBO}$	$V_{CE} = -4.5V$ $I_E = 0$	-	2.5	-	2.5	-	-	-	-	-	-	-	-	nA
Collector-Base Leakage Current	$I_{CBO}$	$V_{CE} = -4.5V$ $I_E = 0, T_{emp}: +65^\circ\text{C}$	-	50	-	50	-	-	-	-	-	-	-	-	nA
Emitter-Base Leakage Current	$I_{EBO}$	$V_{EB} = -4.5V$ $I_C = 0$	-	2.5	-	2.5	-	-	-	-	-	-	-	-	nA
Emitter-Collector Inverse Leakage Current	$I_{EC}$	$V_{CE} = -10V$ $V_{EC} = -15V$	-	-	-	-	-	1.5	-	2.5	-	10.0	-	10.0	nA
Emitter Offset Current	$I_{E1}$	$V_{CE} = -1.5V$	-	1.0	-	3.0	-	1.0	-	1.5	-	2.0	-	2.0	nA
Emitter Offset Voltage	$V_{E1}$	$I_E = -250\mu\text{A}$ $I_C = 0$	-	1.0	-	3.0	-	2.0	-	3.0	-	4.0	-	4.0	mV
Collector Saturation Voltage	$V_{CE(sat)}$	$I_E = -500\mu\text{A}$ $I_C = -20\mu\text{A}$	-	-	-	-	-	3.0	-	4.0	-	5.0	-	5.0	mV
A.C. Current Gain	$h_{fe}$	$V_{CE} = -6V$ $I_E = 1.0\text{mA}$ $f = 1\text{KC}$	25	-	25	-	-	-	-	-	-	-	-	-	-
High Frequency Current Gain	$h_{fe}$	$V_{CE} = -6V$ $I_E = 1.0\text{mA}$ $f = 1\text{MC}$	16	-	16	-	1.0	-	1.0	-	1.0	-	1.0	-	-
Collector to Base Capacitance	$C_{ob}$	$V_{CE} = -6V$ $I_E = -1.0\text{mA}$ $f = 1\text{MC}$	-	14	-	14	-	14	-	14	-	14	-	14	pf

